

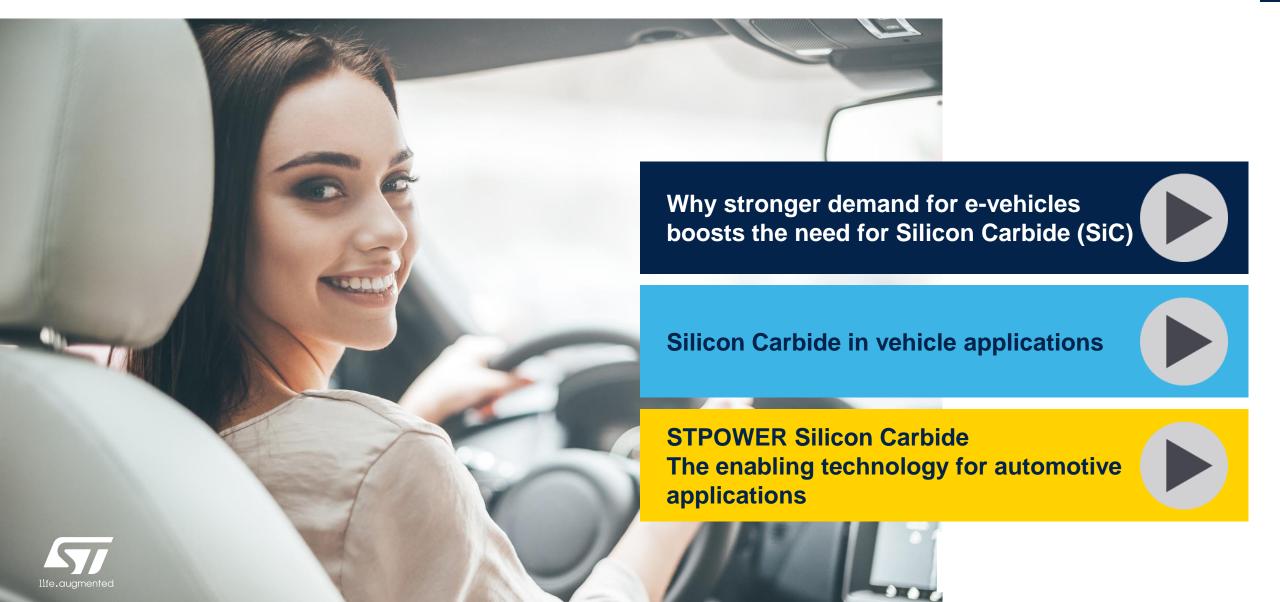


SiC power modules for your electric vehicle design

STMicroelectronics



STPOWER Silicon Carbide (SiC) MOSFET offers for electric vehicles



Why stronger demand for electric vehicles boosts the need for SiC



Higher efficiency and extended vehicle range

Smaller form cost and weight

Less cooling effort and faster recharging

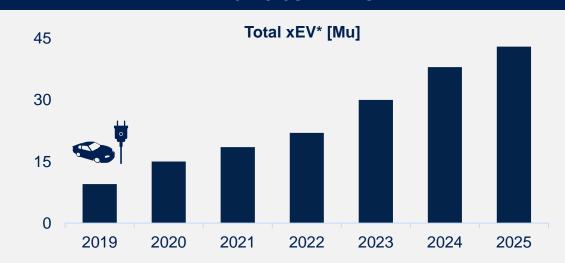




Electrification Market Outlook

Electrification Boosted by Power Silicon & New Materials will Accelerate Growth of a Flattish Light Vehicles Market

Continuous and Consistent Growth of Electrified Light Vehicles - xEVs



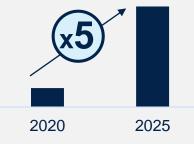
- Total Electrified Vehicle CAGR '19-'25 → >28%
- By 2025 Battery Electric Vehicles will be >25% of Total Electrified Vehicles

Silicon Carbide allows Battery Electric Vehicles to go Beyond the Limits of Silicon

Replacing Silicon based IGBTs and Diodes in the **Traction Inverter** and **On-Board Charger** by **SiC MOSFETs** resulting in:

- Higher efficiency
- Smaller form cost & weight
- Less cooling effort
- Faster recharging
- Extended vehicle range

Today >40% BEVs are using SiC





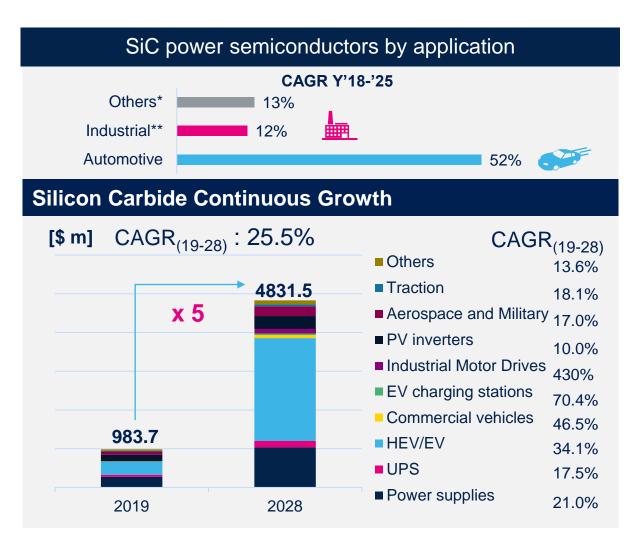


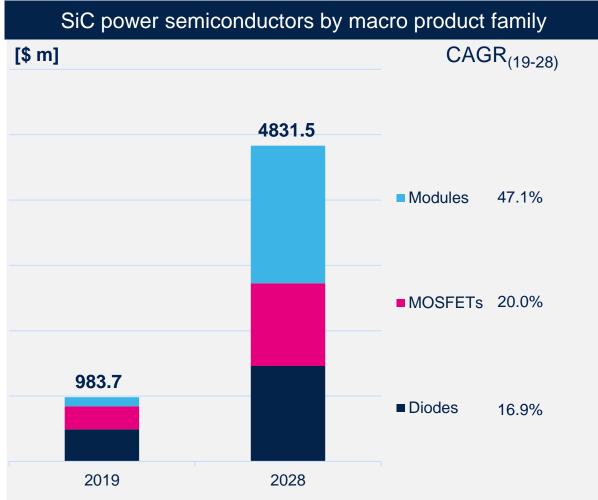






Silicon Carbide Market Outlook







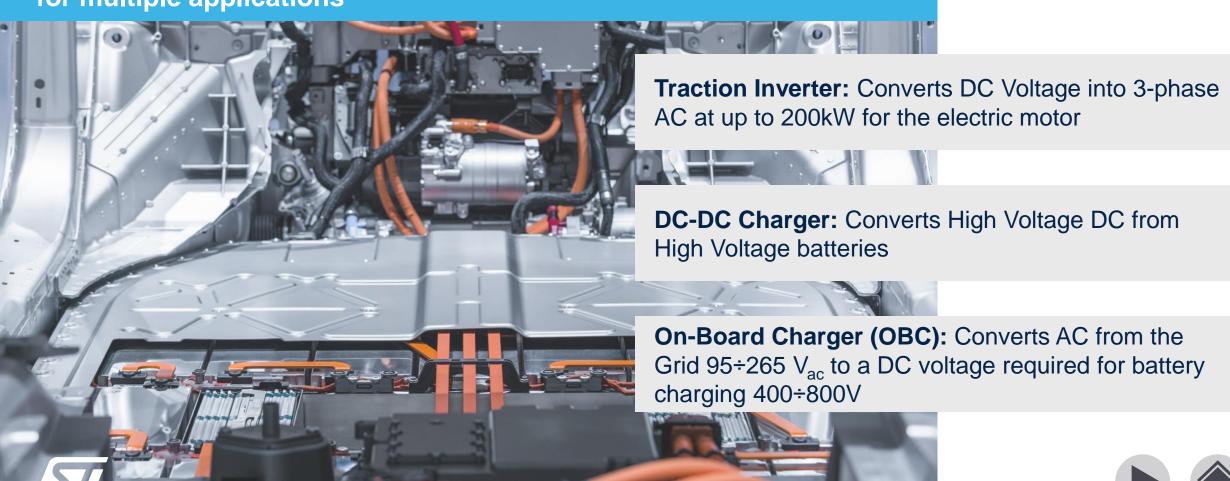






Silicon Carbide in electric vehicle applications

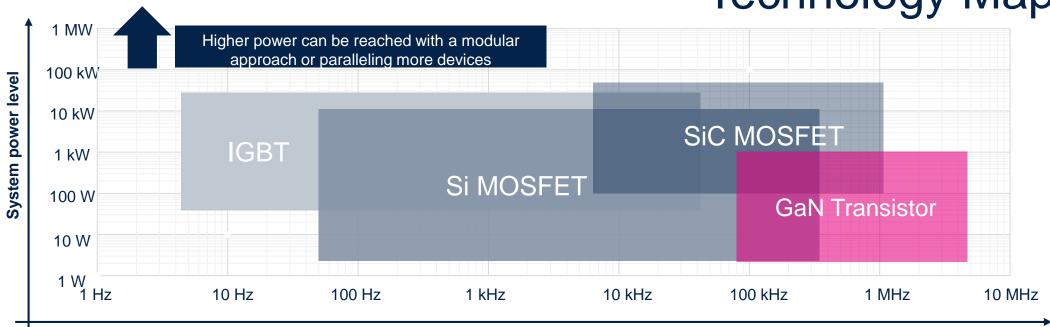
One key technology based on Wide Band Gap (WBG) semiconductors for multiple applications







Wide Band Gap Technology Mapping



Operating frequency

Technology	Features	Preferred for (some example)			
Si HV MOSFET	Medium-high power, high voltage, up to several kW, high frequency	SMPS, server and telecom, DC/DC, low power motor control, OBC, charging station,			
IGBT	Very high power, high voltage, medium frequency up to 50 kHz	HV motor control, H.A., UPS, welding, induction heating, main traction,			
SIC MOSFET	Very high power, high voltage, high frequency, high temperature ratings	High power DC/DC, UPS, charging station, main traction inverters, OBC,			
GaN Transistor	Very high frequency > 80 kHz, medium-high power up to several kW	SMPS, Telecom Power, DC/DC, OBC, PV inverters, LiDAR,			

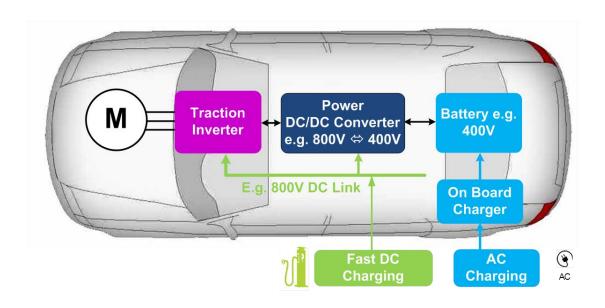




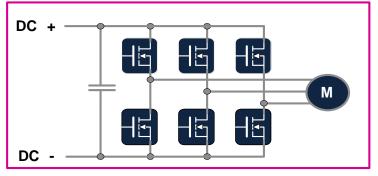




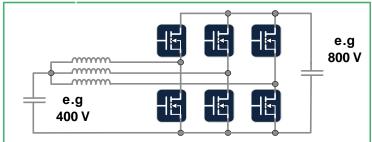
Electric vehicles applications



Traction Inverter



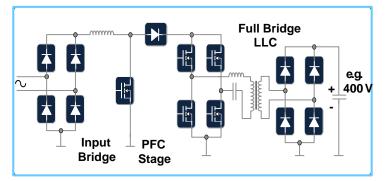
HV DC-DC Converter



• **SiC MOSFETs**, results in **higher efficiency**, smaller form factor, less complexity in cooling Vs. Si approach

High power DC-DC converter for fast and reliable **DC**Charging reduces the charging time of HEVs and EVs

On-Board Charger



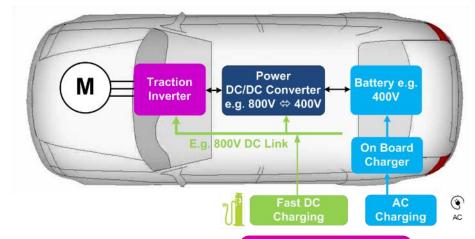


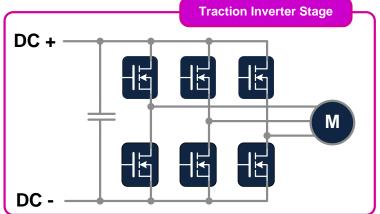




SiC technology for traction inverter

To enhance traction inverter efficiency





- High power inverter stage to drive the vehicle traction motor.
- Replacing silicon based IGBTs and diodes in the inverter stage by SiC MOSFETs, results in higher efficiency, smaller form factor, less cooling requirements, ...
- Comprehensive ST portfolio of STPOWER SiC MOSFETs as bare die, package or module solution in 650 V as well as 1200 V technology.

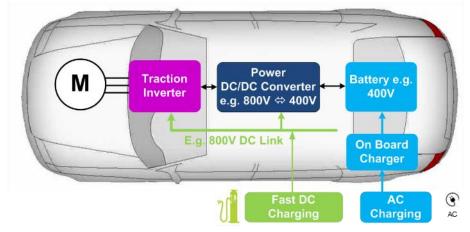


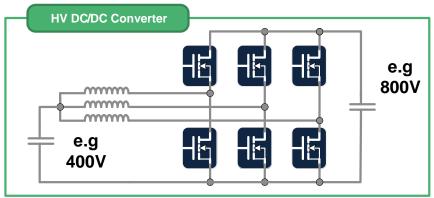




SiC technology for HV DC-DC converter

To minimize conduction and switching losses





- High voltage DC-DC converter to boost battery voltage up, enabling operation of the traction motor within optimized voltage range.
- High voltage DC-DC converter for fast and reliable
 DC Charging in dual voltage domains reducing significantly the charging time of HEVs and EVs.
- STPOWER SiC MOSFET solutions from ST operate at higher switching frequency and at higher temperature enabling
 - minimized magnetic losses
 - a smaller, lighter cooling system
 - the highest power levels



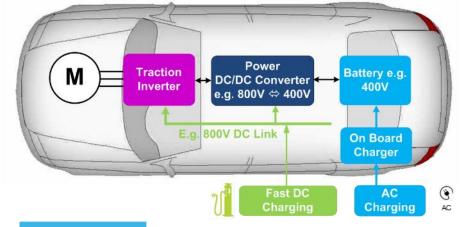


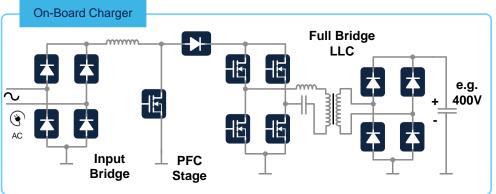




SiC technology for on-board charger

To speed-up systems charging time





- Charging the battery of plug-in HEVs and EVs from the single-phase or 3-phase power grid.
- Different architectures and topologies in automotive are required to support scalable solutions.
- ST solutions enable compact and efficient designs
 - STPOWER SiC MOSFETs & SiC Diodes
 - STPOWER SJ MOSFETs, IGBTs, fast Diodes & SCRs

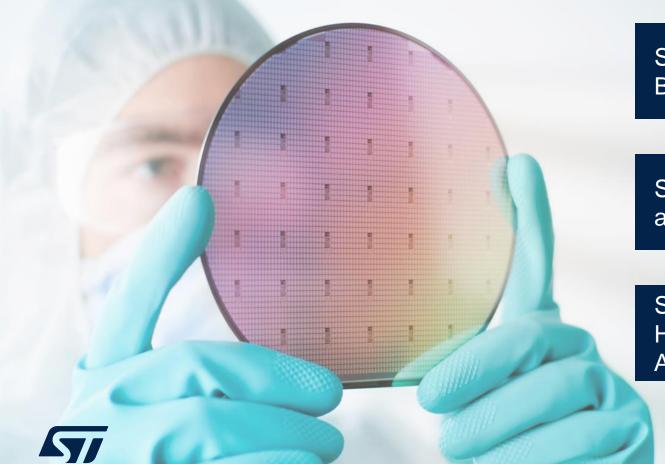






STPOWER Silicon Carbide The enabling technology for automotive application

ST best-in-class SiC Technology



ST offers a broad range of SiC solutions: Discrete, Bare Dice, Module

ST continue capacity expansion to support market acceleration

ST invests on advanced package technologies with HiP247-4™ leads, HU3PAK™, STPAK™, ACEPACK™ SMIT





STPOWER SiC MOSFET families Overview

The best high voltage and high frequency switch for high density applications



Gen1

1200V-1700V

Gen2

650V, 1200V

Gen3

650V, 750V, 900V, 1200V

The best option for **R**_{ON} **vs. Tj** behavior: highly suitable for motor drive applications

The best R_{ON} vs. Q_g trade-off: highly suitable for a broad range of automotive and industrial applications

An ultra-fast series with the **best** R_{oN} **vs.** Q_g **trade off:** highly suitable for very high frequency applications



SiC MOSFET: the true R-evolution for high voltage power switches









STPOWER Silicon Carbide the enabling technology for automotive applications

Silicon Carbide product portfolio

AG 650V SiC MOSFETs: Gen 2 High Voltage Product Family in production

- SCTx35N65xx
- SCTx100N65xx



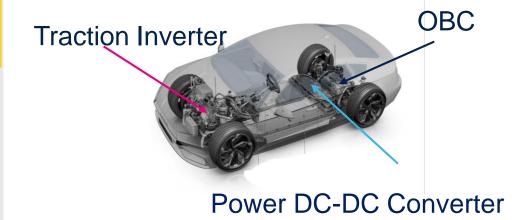




HiP247™



Main applications



AG 1200V SiC MOSFETs: Gen 2 Very High Voltage High Product Family in Production

- SCTx40N120xx
- SCTx70N120xx
- SCTx100N120xx







HiP247™



Key benefits

- Smaller form factor with high power density
- Higher system efficiency at high frequency
- Reduced size/cost of passive components
- Low power losses at high temperatures
- Compact design and cost-effective system approach
- Simpler topologies











STPOWER ACEPACK* module Adaptable Compact Easier PACKage

Option

Key features

Configurations

Target Applications

A1 - A2 (*)



- 100% controlled by ST for SiC, MOSFETs, **IGBTs** and Diodes
- Compact design and cost-effective system approach for a plug & play system solution
- Configuration flexibility
- 2500 V_{RMS} electrical isolation

- CIB
- Six-pack
- Three level
- Boost interleaved

SMIT (**)





- 2500 V_{RMS} electrical isolation
- SMD assembly
- Total footprint 32.7 x 22.5 mm
- Top side cooling
- Low thermal resistance

- Bridge rectifier
- Half-bridge
- Single-boost





- Optimized for 200 kW inverters
- SiC MOSFET based switch
- Improved light load power losses for extended EV driving ranges
- Extreme low conduction losses
- Short circuit ruggedness
- Direct cooled Cu base plate with pin fins















(*) available (**) Engineering Samples available

Six-pack



STPOWER SiC MOSFET product portfolio by application

Breakdown Voltage ————————————————————————————————————									
650 V		750 V	1200 V			1700 V			
Series —————									
Gen2	Gen3	Gen3	Gen1	Gen2	Gen3	Gen1			
On-state resistance									
18 mOhm to 55 mOhm	55 mOhm	11 mOhm	52 mOhm to 520 mOhm	25 mOhm to 75 mOhm	70 mOhm and 15 mOhm	1 Ohm and 65 mOhm			
Focus Applications —————									
OBC & DC-DC Renewable energy Power Supply Industrial drives	OBC & DC-DC Power Supply Solar	DC-DC Renewable energy	Photovoltaic HVAC Power supply	OBC & DC-DC Inverter Street Lighting Charging stations Industrial drives	Inverter DC-DC Power Supply	DC-DC Power Supply Renewable energy			









30+ years' experience with STPOWER and Discrete The success factor of fast growing EV market

GaN HEMT 650 V and 100 V normally off solutions to boost efficiency and power density thanks to fast switching operation 48V DC-DC

HV Si MOSFET: MDmesh Super-Junction MultiDrain







OBC and **DC-DC** converter

IGBT

High Power IGBT Trench Field-stop

Narrow MESA



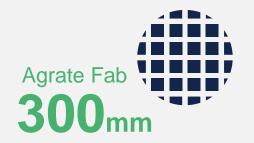






ST commitment

Investing in new facilities to sustain Power Silicon growth



Continue innovation on Power Package



















2SPAK

PowerFLAT 8x8 DSC

STPAK

TO-LL

PowerFLAT 8x8 HV

HU3PAK

ACEPACK SMIT

ACEPACK 1, 2

ACEPACK DRIVE



OBC







Thank you



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